



## BUL128D-B

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

### APPLICATIONS:

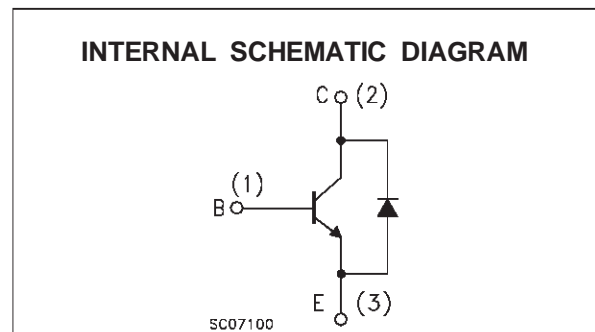
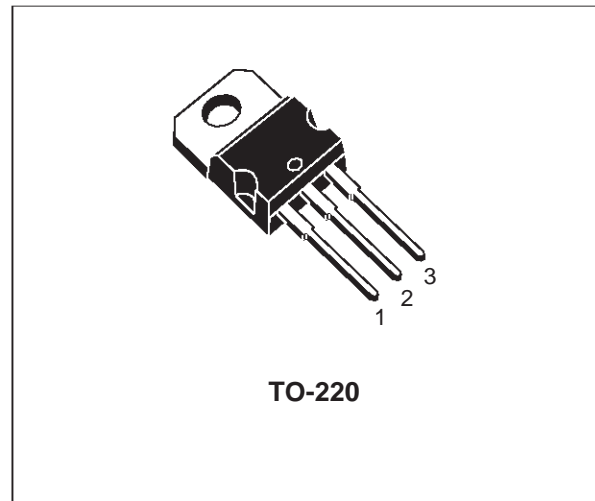
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS

### DESCRIPTION

The device is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and medium voltage capability.

It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The device is designed for use in lighting applications and low cost switch-mode power supplies.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	700	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	400	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	9	V
$I_C$	Collector Current	4	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	8	A
$I_B$	Base Current	2	A
$I_{BM}$	Base Peak Current ( $t_p < 5$ ms)	4	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	70	W
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

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### THERMAL DATA

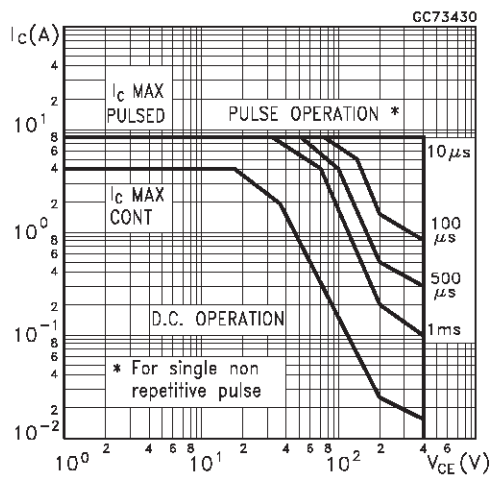
R <sub>thj-case</sub>	Thermal Resistance Junction-Case	Max	1.78	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-Ambient	Max	62.5	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

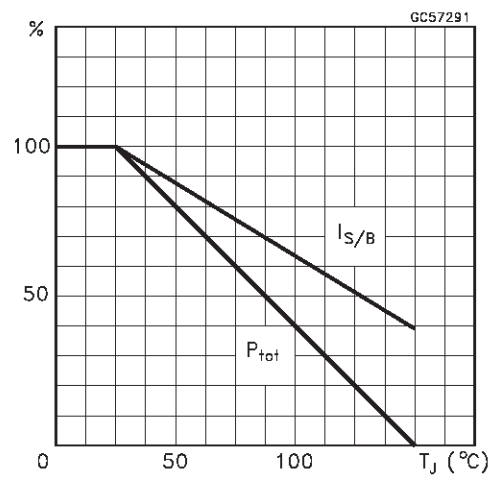
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5 V)	V <sub>CE</sub> = 700 V			100	μA
		V <sub>CE</sub> = 700 V      T <sub>j</sub> = 125 °C			500	μA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 400 V			250	μA
V <sub>EBO</sub>	Emitter-Base Voltage	I <sub>E</sub> = 10 mA	9			V
V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100 mA      L = 25 mH	400			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5 A      I <sub>B</sub> = 0.1 A			0.7	V
		I <sub>C</sub> = 1 A      I <sub>B</sub> = 0.2 A			1.0	V
		I <sub>C</sub> = 2.5 A      I <sub>B</sub> = 0.5 A			1.5	V
		I <sub>C</sub> = 4 A      I <sub>B</sub> = 1 A		0.5		V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 0.5 A      I <sub>B</sub> = 0.1 A			1.1	V
		I <sub>C</sub> = 1 A      I <sub>B</sub> = 0.2 A			1.2	V
		I <sub>C</sub> = 2.5 A      I <sub>B</sub> = 0.5 A			1.3	V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 10 mA      V <sub>CE</sub> = 5 V	10			
		I <sub>C</sub> = 2 A      V <sub>CE</sub> = 5 V	8		40	
V <sub>f</sub>	Forward Voltage Drop	I <sub>f</sub> = 2 A			2.5	V
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	V <sub>CC</sub> = 200 V      I <sub>C</sub> = 2 A				
		I <sub>B1</sub> = 0.4 A      V <sub>BE(off)</sub> = -5 V R <sub>BB</sub> = 0 Ω      L = 200 μH (see fig.1)		0.6 0.1		μs μs
t <sub>s</sub> t <sub>f</sub>	RESISTIVE LOAD Storage Time Fall Time	V <sub>CC</sub> = 250 V      I <sub>C</sub> = 2 A				
		I <sub>B1</sub> = 0.4 A      I <sub>B2</sub> = -0.4 A T <sub>p</sub> = 30 μs      (see fig.2)	2	0.2	2.9	μs μs

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

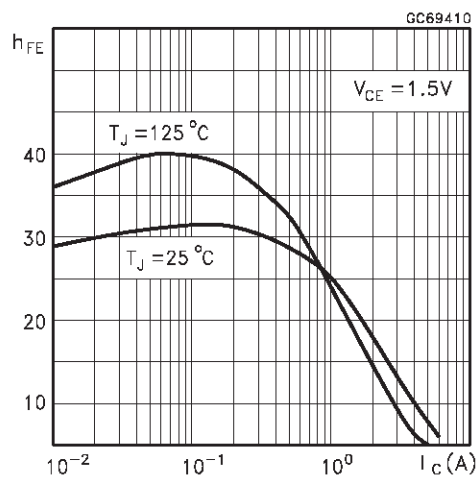
Safe Operating Areas



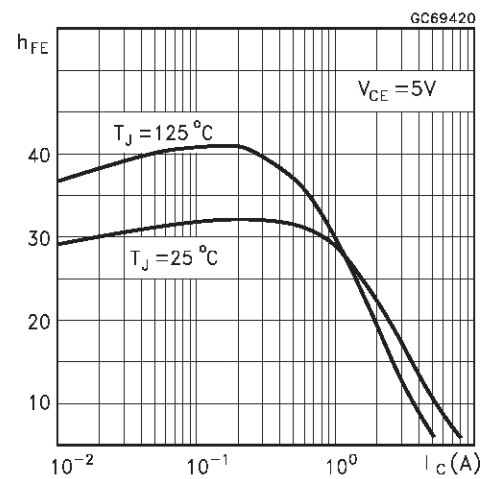
Derating Curve



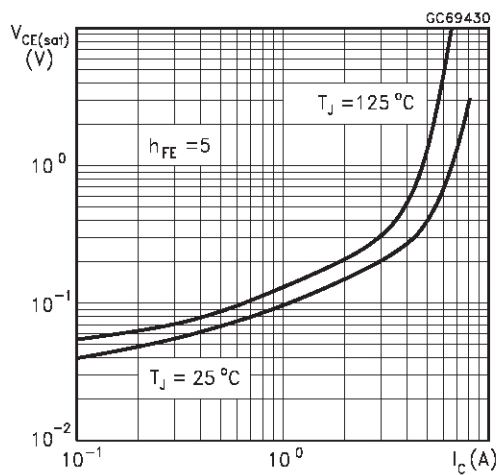
DC Current Gain



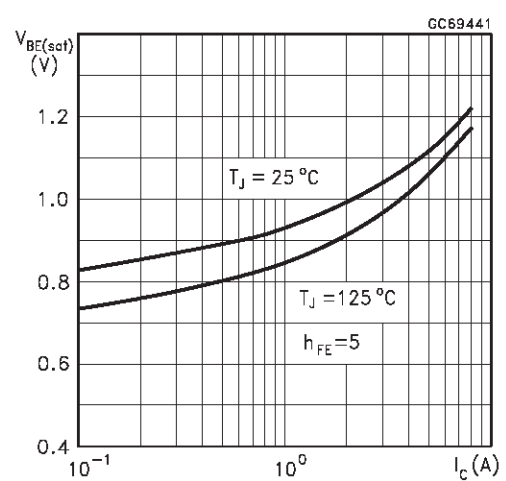
DC Current Gain



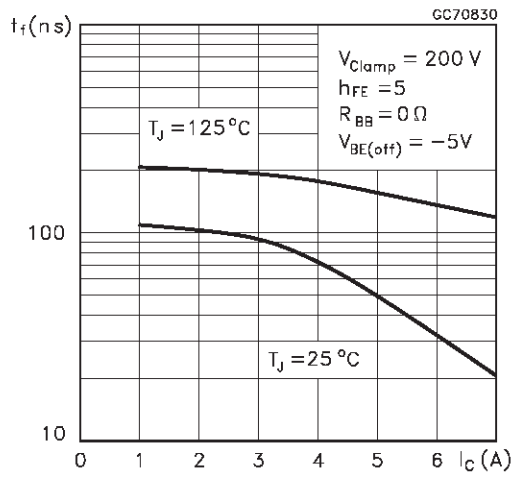
Collector Emitter Saturation Voltage



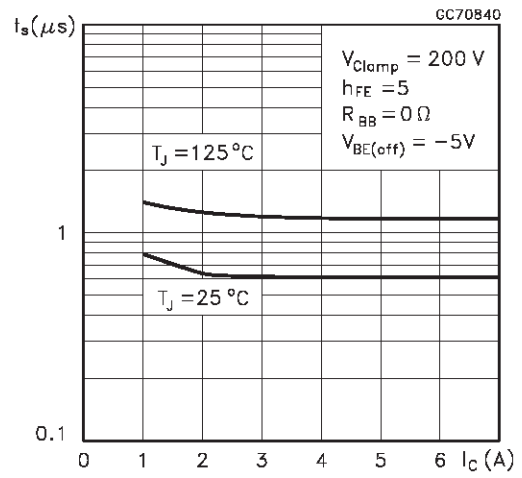
Base Emitter Saturation Voltage



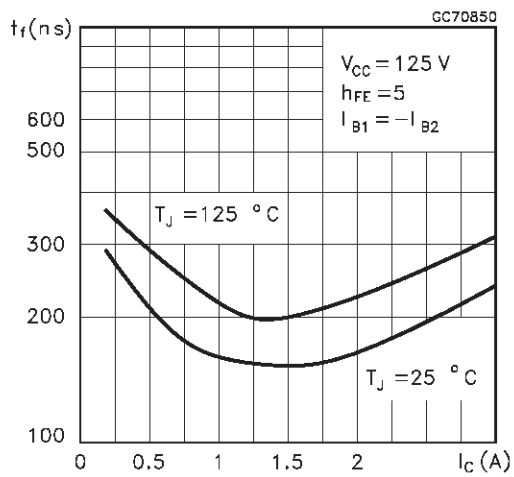
Inductive Fall Time



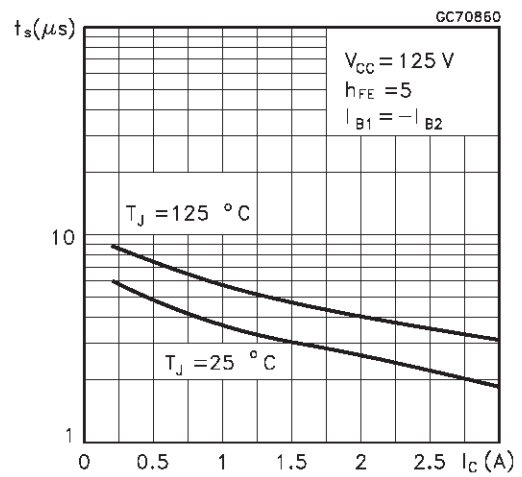
Inductive Storage Time



Resistive Load Fall Time



Resistive Load Storage Time



Reverse Biased SOA

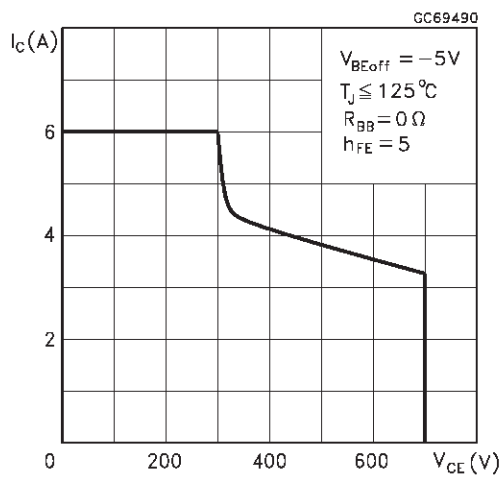


Figure 1: Inductive Load Switching Test Circuits.

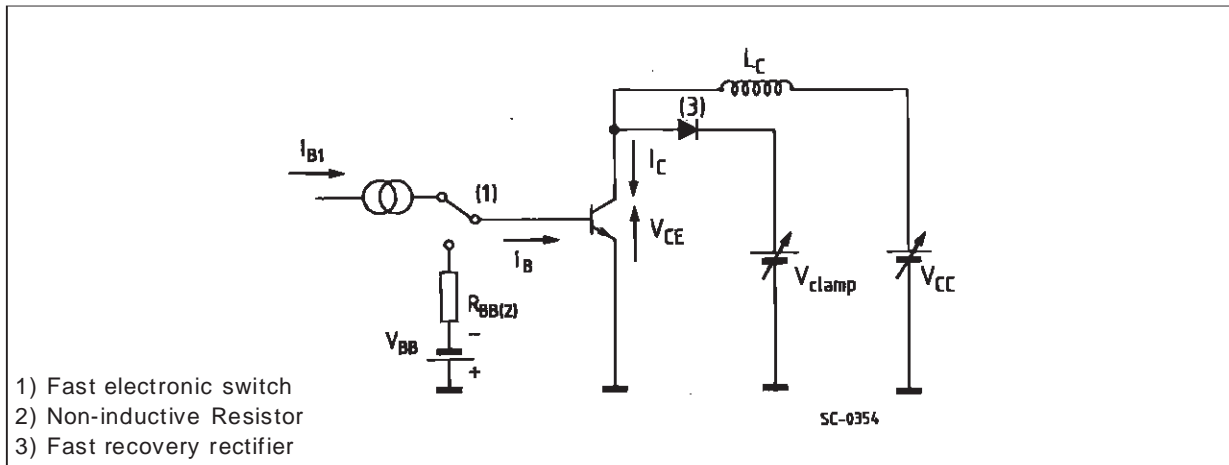
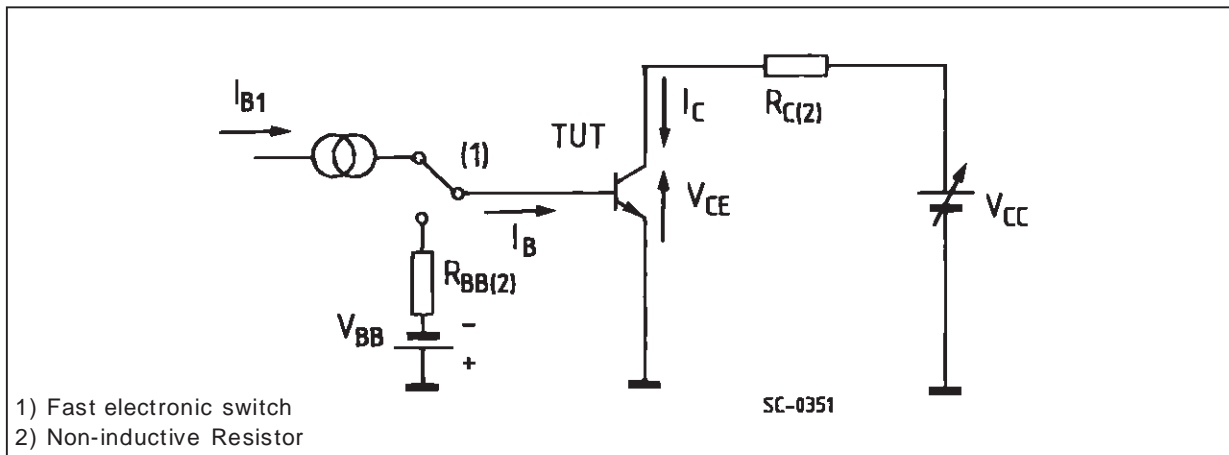
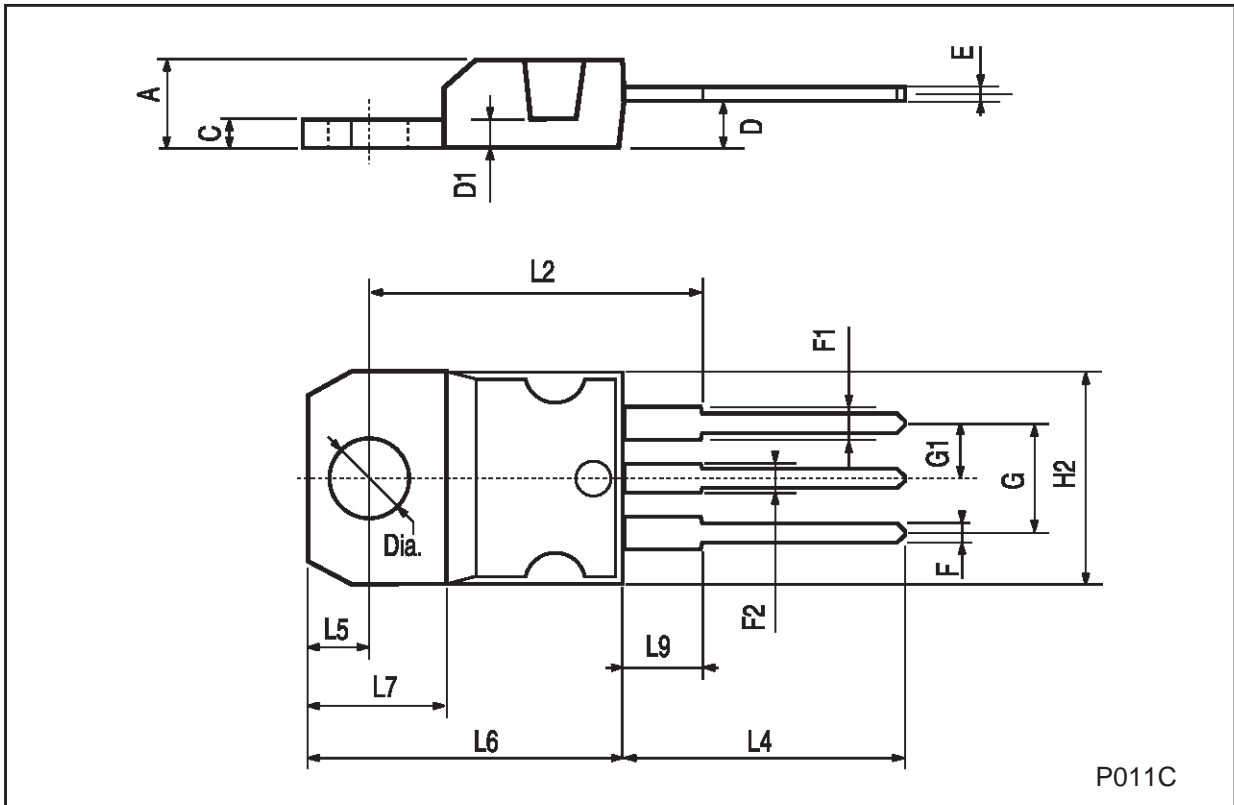


Figure 2: Resistive Load Switching Test Circuits.



**TO-220 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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